The optimal multilevel Monte-Carlo approximation of the stochastic drift-diffusion-Poisson system

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arXiv:1610.04521v1 [math.AP] 14 Oct 2016

Abstract

Existence and local-uniqueness theorems for weak solutions of a system consisting of the drift-diffusion-Poisson equations and the Poisson-Boltzmann equation, all with stochastic coefficients, are presented. For the numerical approximation of the expected value of the solution of the system, we develop a multi-level Monte-Carlo (MLMC) finite-element method (FEM) and we analyze its rate of convergence and its computational complexity. This allows to find the optimal choice of discretization parameters. Finally, numerical results show the efficiency of the method. Applications are, among others, noise and fluctuations in nanoscale transistors, in field-effect bio- and gas sensors, and in nanopores.

Keywords: Stochastic drift-diffusion-Poisson system, existence and uniqueness, multi-level Monte-Carlo finite-element method, optimal method.

1. Introduction

In this work, we consider the system consisting of the drift-diffusion-Poisson equations coupled with the Poisson-Boltzmann equation, all with random coefficients. We show existence and local uniqueness of weak solutions for the stationary problem. This system is a general model for transport processes, where a stochastic process determines the coefficients. Furthermore, we develop a multi-level (ML) Monte-Carlo (MC) finite-element method (FEM) for the system of equations. The different types of errors in the numerical approximation must be balanced and the optimal approach is found here.

In the system of equations considered here, both the operators and the forcing terms are stochastic, and therefore this system has numerous applications (see Figure 1). A deterministic and simplified version, without the Poisson-Boltzmann equation, is the standard model for semiconductor devices. Nowadays, randomness due to the location of impurity atoms is the most important effect limiting the design of integrated circuits. This application area is included in the present model equations. Furthermore, the full system of equations considered here describes a very general class of field-effect sensors including their most recent incarnation, nanowire bio- and gas sensors. While previous mathematical modeling has focused on the deterministic problem and stochastic surface reactions [1, 2, 3, 4, 5, 6], the present model describes how various stochastic processes propagate through a PDE model and result in noise and fluctuations in a transport model. Quantifying noise and fluctuations in sensors is important, since they determine the detection limit and the signal-to-noise ratio. Noise and fluctuations are of great importance especially in nanometer-scale devices, as any random effect becomes proportionally more important as devices are shrunk.

Various sources of noise and fluctuations are included in the model equations here. Doping of semiconductor devices is inherently random and results in a random number of impurity atoms placed at random positions, each one changing the charge concentration and the mobility at its location. In field-effect sensors, target molecules bind to randomly placed probe molecules in a stochastic process, so that the detection mechanism is inherently stochastic.

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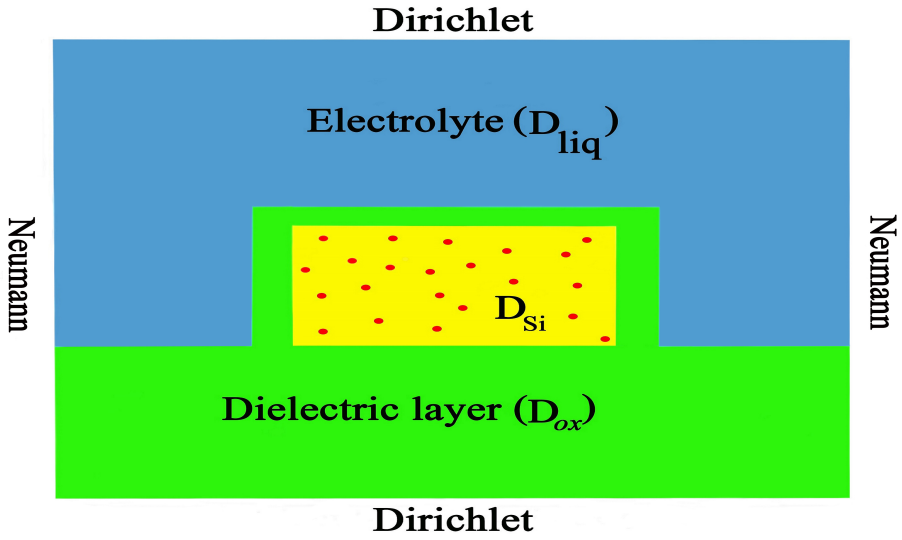

Figure 1: Schematic diagram showing leading applications. In a field-effect transistor, the dopant atoms are randomly distributed (there is no electrolyte). In field-effect sensors, there are randomly distributed dopant atoms as well as randomly distributed charged molecules in the electrolyte.

The Brownian motion of the target molecules also results in changes in charge concentration and permittivity. This randomness at the sensor surface propagates through the self-consistent transport equations and finally results in noise in the sensor output.

In summary, there are many applications where both the operators and the forcing terms in the drift-diffusion-Poisson system are random. The probability distributions of permittivities and charge concentrations can be calculated from physical models [7].

In many realistic situations, the probability space is high-dimensional. For example, each probe molecule, each target molecule, and each probe-target complex needs to be modeled in sensors. In transistors, the number impurities and their positions are random. The large number of dimensions favors the use of Monte-Carlo (MC) methods: It is well-known that the convergence rate of standard MC methods is independent of the number of dimensions. On the other hand, it is inversely proportional to the square root of the number of evaluations and here each evaluation requires solving a two- or three-dimensional system of elliptic equations.

These considerations motivate the development of a multi-level Monte-Carlo (MLMC) algorithm. In [8], after earlier work [9] on numerical quadrature, it was shown that a multi-level approach and a geometric sequence of timesteps can reduce the order of computational complexity of MC path simulations for estimating the expected value of the solution of a stochastic ordinary differential equation. This is done by reducing the variance and leaving the bias unchanged due to the Euler discretization used as the ODE solver. In [10], the Milstein scheme was used as the ODE solver to improve the convergence rate of the MLMC method for scalar stochastic ordinary differential equations and the method was made more efficient. The new method has the same weak order of convergence, but an improved first-order strong convergence, and it is the strong order of convergence which is central to the efficiency of MLMC methods. In [11], the MLMC method was combined with quasi-Monte-Carlo (QMC) integration using a randomized rank-1 lattice rule and the asymptotic order of convergence of MLMC was improved and a lower computational cost was achieved as well.

In [12], an MLMC finite-element method was presented for elliptic partial differential equations with stochastic coefficients. In this problem, the source of randomness lies in the coefficients inside the operator and the coefficient fields are bounded uniformly from above and away from zero. The MLMC error and work estimates were given for the expected values of the solutions and for higher moments. Also, in [13], the same problem was considered and numerical results indicate that the MLMC estimator is not limited to smooth problems. In [14], a multi-level quasi-Monte-Carlo finite-element method for a class of elliptic PDEs with random coefficients was presented. The

error analysis of QMC was generalized to a multi-level scheme with the number of QMC points dependent on the discretization level and with a level-dependent dimension truncation strategy.

In [15], uniform bounds on the finite-element error were shown in standard Bochner spaces. These new bounds can be used to perform a rigorous analysis of the MLMC method for elliptic problems, and a rigorous bound on the MLMC complexity in a more general case was found. In [16], the finite-element error analysis was extended for the same type of equations posed on non-smooth domains and with discontinuities in the coefficient. In [17], a general optimization of the parameters in the MLMC discretization hierarchy based on uniform discretization methods with general approximation orders and computational costs was developed. In current work, we define a global optimization problem which minimizes the computational complexity such that the error bound is less or equal to a given tolerance level.

The rest of this paper is organized as follows. In Section 2, we present the system of model equations with stochastic coefficients in detail. In Section 3, we define weak solutions of the model equations and prove existence and local-uniqueness theorems. Section 4.1 collects results about the FEM for later use. In Section 4, we introduce a multi-level Monte-Carlo finite-element method for the system and analyze its rate of convergence. In Section 5, we discuss the computational complexity and find the optimal MLMC method. In Section 6, we present numerical results for random impurity atoms in nanowire field-effect sensors. The MLMC-FEM method is illustrated there and the computational costs of various numerical techniques are compared as well. Finally, conclusions are drawn in Section 7.

2. The Stochastic Model Equations

Suppose that the domain $D \subset \mathbb{R}^d$ is bounded and convex, and that $d \leq 3$. The whole domain D is partitioned into three subdomains with different physical properties and hence different model equations in order to include a large range of applications. The first subdomain D_{Si} consists of the (silicon) nanowire and acts as the transducer of the sensor; in this subdomain, the drift-diffusion-Poisson system describes charge transport. The semiconductor is surrounded by a dielectric layer (usually an oxide) which comprises the second subdomain D_{ox}, where just the Poisson equation holds. Finally, the third subdomain D_{liq} is the aqueous solution containing cations and anions and the Poisson-Boltzmann equation holds. Also, the boundary layer at the sensor surface is responsible for the recognition of the target molecules. In the case of field-effect sensors, solving a homogenization problem gives rise to two interface conditions for the Poisson equation [1]. In summary, the domain is partitioned into

$$D = D_{\mathrm{Si}} \cup D_{\mathrm{ox}} \cup D_{\mathrm{liq}}.$$

In the subdomain D_{Si}, the stationary drift-diffusion-Poisson system

$$-\nabla \cdot (A(x,\omega)\nabla V(x,\omega)) = q(C_{\mathrm{dop}}(x,\omega) + p(x,\omega) - n(x,\omega)), \tag{1a}$$

$$\nabla \cdot J_n(x,\omega) = qR(n(x,\omega), p(x,\omega)), \tag{1b}$$

$$\nabla \cdot J_p(x,\omega) = -qR(n(x,\omega), p(x,\omega)), \tag{1c}$$

$$J_n(x,\omega) = q(D_n \nabla n(x,\omega) - \mu_n n(x,\omega)\nabla V(x,\omega)), \tag{1d}$$

$$J_p(x,\omega) = q(-D_p \nabla p(x,\omega) - \mu_p p(x,\omega)\nabla V(x,\omega)) \tag{1e}$$

models charge transport, where $A(x,\omega)$, the permittivity, is a random field with $x \in \mathbb{R}^d$ and a random parameter $\omega \in \Omega$ in a probability space $(\Omega, \mathbb{A}, \mathbb{P})$. Ω denotes the set of elementary events, i.e., the sample space, $\mathbb{A}$ the σ-algebra of all possible events, and $\mathbb{P}\colon \mathbb{A} \to [0,1]$ is a probability measure. $V(x,\omega)$ is the electrostatic potential and $q > 0$ is the elementary charge, $C_{\mathrm{dop}}(x,\omega)$ is the doping concentration, $n(x,\omega)$ and $p(x,\omega)$ are the concentrations of electrons and holes, respectively, $J_n(x,\omega)$ and $J_p(x,\omega)$ are the current densities, D_n and D_p are the diffusion coefficients, μ_n and μ_p are the mobilities, and $R(n(x,\omega), p(x,\omega))$ is the recombination rate. We use the Shockley-Read-Hall recombination rate

$$R(n(x,\omega), p(x,\omega)) := \frac{n(x,\omega)p(x,\omega) - n_i^2}{\tau_p(n(x,\omega) + n_i) + \tau_n(p(x,\omega) + n_i)}$$

here, where the constant n_i is the intrinsic charge density and τ_n and τ_p are the lifetimes of the free carriers, although the mathematical results here hold for many expressions for the recombination rate. Equations (1) include the convection terms $-n\nabla V$ and $-p\nabla V$, which prohibit the use of the maximum principle in a simple way.

We assume that the Einstein relations $D_n = U_T\mu_n$ and $D_p = U_T\mu_p$ hold, where the constant U_T is the thermal voltage. Therefore, it is beneficial to change variables from the concentrations n and p to the Slotboom variables u and v defined by

$$\begin{aligned} n(x,\omega) &=: n_i \mathrm{e}^{V(x,\omega)/U_T} u(x,\omega), \\ p(x,\omega) &=: n_i \mathrm{e}^{-V(x,\omega)/U_T} v(x,\omega). \end{aligned}$$

The system (1) then becomes

$$\begin{aligned} -\nabla\cdot(A\nabla V(x,\omega)) &= q n_i (e^{-V(x,\omega)/U_T} v(x,\omega) - e^{V(x,\omega)/U_T} u(x,\omega)) + q C_{\mathrm{dop}}(x,\omega), \\ U_T\nabla\cdot(\mu_n e^{V(x,\omega)/U_T}\nabla u(x,\omega)) &= \frac{u(x,\omega)v(x,\omega)-1}{\tau_p(e^{V(x,\omega)/U_T}u(x,\omega)+1)+\tau_n(e^{-V(x,\omega)/U_T}v(x,\omega)+1)}, \\ U_T\nabla\cdot(\mu_p e^{-V(x,\omega)/U_T}\nabla v(x,\omega)) &= \frac{u(x,\omega)v(x,\omega)-1}{\tau_p(e^{V(x,\omega)/U_T}u(x,\omega)+1)+\tau_n(e^{-V(x,\omega)/U_T}v(x,\omega)+1)}, \end{aligned}$$

where the continuity equations are self-adjoint.

The boundary ∂D is partitioned into Dirichlet and Neumann boundaries. For the Ohmic contacts we have

$$V(x,\omega)|_{\partial D_D} = V_D(x), \quad u(x,\omega)|_{\partial D_{\mathrm{Si},D}} = u_D(x) \quad \text{and} \quad v(x,\omega)|_{\partial D_{\mathrm{Si},D}} = v_D(x).$$

At Ohmic contacts the space charge vanishes, i.e., $C_{\mathrm{dop}} + p_D - n_D = 0$, and the system is in thermal equilibrium, i.e., $n_D p_D = n_i^2$ on ∂D_D. Furthermore, at each contact, the quasi Fermi potential levels of silicon are aligned with an external applied voltage $U(x)$. Therefore, by using the quasi Fermi potential, we determine the boundary condition on $\partial D_{\mathrm{Si},D}$ using

$$V_1(x) := U(x) + U_T \ln\left(\frac{n_D(x)}{n_i}\right) = U(x) - U_T \ln\left(\frac{p_D(x)}{n_i}\right).$$

The boundary values $u_D(x)$ and $v_D(x)$ are found to be

$$\begin{aligned} u_D(x) &:= n_i^{-1} e^{-V_1(x)/U_T} n_D(x), \\ v_D(x) &:= n_i^{-1} e^{V_1(x)/U_T} p_D(x), \end{aligned}$$

where

$$\begin{aligned} n_D(x) &:= \frac{1}{2}\left(C_{\mathrm{dop}} + \sqrt{C_{\mathrm{dop}}^2 + 4n_i^2}\right), \\ p_D(x) &:= \frac{1}{2}\left(-C_{\mathrm{dop}} + \sqrt{C_{\mathrm{dop}}^2 + 4n_i^2}\right) \end{aligned}$$

hold [18, Chapter 3]. Here, $C_{\mathrm{dop}} := N_D^+ - N_A^-$ is the net doping concentration, where N_D^+ and N_A^- are the donor and acceptor concentrations, respectively.

The zero Neumann boundary conditions

$$\mathbf{n}\cdot\nabla V(x,\omega) = 0, \quad \mathbf{n}\cdot\nabla u(x,\omega) = 0, \quad \mathbf{n}\cdot\nabla v(x,\omega) = 0$$

hold on the rest of the boundary ∂D. Here $\mathbf{n}$ denotes the unit outward normal vector on the boundary.

A jump in the permittivity A always gives rise to two continuity conditions: the continuity of the potential and the continuity of the electric displacement field. Homogenization of an elliptic problem with a periodic boundary layer at a manifold Γ yields the two interface conditions [1]

$$\begin{aligned} V(0+,y,\omega) - V(0-,y,\omega) &= \alpha(y,\omega), \\ A(0+)\partial_x V(0+,y,\omega) - A(0-)\partial_x V(0-,y,\omega) &= \gamma(y,\omega) \end{aligned}$$

between the semiconductor and the liquid. Here we denote the one-dimensional coordinate orthogonal to the manifold Γ by x and the remaining $(d-1)$-dimensional coordinates by y. α and γ are essentially given by the dipole-moment and the surface-charge densities of the boundary layer; in general, we write them as the functional $M_\alpha(V)$ and $M_\gamma(V)$ of the potential V. They may correspond to the Metropolis Monte-Carlo method [19], to solving the nonlinear Poisson-Boltzmann equation [7], or to systems of ordinary differential equations for surface reactions [20, 21].

In the subdomain D_{ox}, there are no charge carriers and the Poisson equation is simply

$$-\nabla \cdot (A \nabla V(x,\omega)) = 0.$$

In the subdomain D_{liq}, the nonlinear Poisson-Boltzmann equation

$$-\nabla \cdot (A(x,\omega)\nabla V(x,\omega)) + 2\eta \sinh(\beta(V(x,\omega) - \Phi(x,\omega))) = 0$$

holds and models screening by free charges. Here η is the ionic concentration, the constant β equals $\beta := q/(k_B T)$ in terms of the Boltzmann constant k_B and the temperature T, and Φ is the Fermi level.

In summary, for all $\omega \in \Omega$, the model equations are the boundary-value problem

$$\begin{aligned}
&-\nabla \cdot (A(x,\omega)\nabla V(x,\omega)) && && \text{(2a)}\\
&= qC_{\text{dop}}(x,\omega) - qn_i(\mathrm{e}^{V(x,\omega)/U_T}u(x,\omega) - \mathrm{e}^{-V(x,\omega)/U_T}v(x,\omega)) && \text{in } D_{\text{Si}}, &\\
&-\nabla \cdot (A(x,\omega)\nabla V(x,\omega)) = 0 && \text{in } D_{\text{ox}}, && \text{(2b)}\\
&-\nabla \cdot (A(x,\omega)\nabla V(x,\omega)) = -2\eta \sinh(\beta(V(x,\omega) - \Phi(x,\omega))) && \text{in } D_{\text{liq}}, && \text{(2c)}\\
&V(0+,y,\omega) - V(0-,y,\omega) = \alpha(y,\omega) && \text{on } \Gamma, && \text{(2d)}\\
&A(0+)\partial_x V(0+,y,\omega) - A(0-)\partial_x V(0-,y,\omega) = \gamma(y,\omega) && \text{on } \Gamma, && \text{(2e)}\\
&U_T \nabla \cdot (\mu_n \mathrm{e}^{V(x,\omega)/U_T}\nabla u(x,\omega)) && && \text{(2f)}\\
&= \frac{u(x,\omega)v(x,\omega) - 1}{\tau_p(\mathrm{e}^{V(x,\omega)/U_T}u(x,\omega) + 1) + \tau_n(\mathrm{e}^{-V(x,\omega)/U_T}v(x,\omega) + 1)} && \text{in } D_{\text{Si}}, &\\
&U_T \nabla \cdot (\mu_p \mathrm{e}^{-V(x,\omega)/U_T}\nabla v(x,\omega)) && && \text{(2g)}\\
&= \frac{u(x,\omega)v(x,\omega) - 1}{\tau_p(\mathrm{e}^{V(x,\omega)/U_T}u(x,\omega) + 1) + \tau_n(\mathrm{e}^{-V(x,\omega)/U_T}v(x,\omega) + 1)} && \text{in } D_{\text{Si}}, &\\
&\alpha(y,\omega) = M_\alpha(V(y,\omega)) && \text{in } \Gamma, && \text{(2h)}\\
&\gamma(y,\omega) = M_\gamma(V(y,\omega)) && \text{in } \Gamma, && \text{(2i)}\\
&V(x,\omega) = V_D(x) && \text{on } \partial D_D, && \text{(2j)}\\
&\mathbf{n} \cdot \nabla V(x,\omega) = 0 && \text{on } \partial D_N, && \text{(2k)}\\
&u(x,\omega) = u_D(x), \quad v(x,\omega) = v_D(x) && \text{on } \partial D_{D,\text{Si}}, && \text{(2l)}\\
&\mathbf{n} \cdot \nabla u(x,\omega) = 0, \quad \mathbf{n} \cdot \nabla v(x,\omega) = 0 && \text{on } \partial D_{N,\text{Si}}. && \text{(2m)}
\end{aligned}$$

3. Existence and Local Uniqueness

In order to state the main theoretical results, we first record the assumptions on the data of the system (2). The assumptions are moderate in the sense that similar ones are necessary for the deterministic system of equations. Then weak solutions and Bochner spaces are defined. Using the assumptions and definitions, existence and local uniqueness are shown.

3.1. Assumptions

The following assumptions are required.

Assumptions 1. 1. *The bounded domain $D \subset \mathbb{R}^3$ has a C^2 Dirichlet boundary ∂D_D, the Neumann boundary ∂D_N consists of C^2 segments, and the Lebesgue measure of the Dirichlet boundary ∂D_D is nonzero. The C^2 manifold $\Gamma \subset D$ splits the domain D into two nonempty domains D^+ and D^- so that meas$(\Gamma \cap \partial D) = 0$ and $\Gamma \cap \partial D \subset \partial D_N$ hold.*

2. $(\Omega, \mathbb{A}, \mathbb{P})$ *is a probability space, where* Ω *denotes the set of elementary events (sample space),* $\mathbb{A}$ *the* σ*-algebra of all possible events, and* $\mathbb{P}\colon \mathbb{A} \to [0,1]$ *is a probability measure.*
3. *The diffusion coefficient* $A(x,\omega)$ *is assumed to be a strongly measurable mapping from* Ω *into* $L^\infty(D)$*. It is uniformly elliptic and bounded function of position* $x \in D$ *and the elementary event* $\omega \in \Omega$*, i.e., there exist constants* $0 < A^- < A^+ < \infty$ *such that*

$$0 < A^- \le \operatorname{ess\,inf}_{x\in D} A(x,\omega) \le \|A(\cdot,\omega)\|_{L^\infty(D)} \le A^+ < \infty \quad \forall \omega \in \Omega.$$

Furthermore, $A(x,\omega)|_{D^+\times\Omega} \in C^1(D^+ \times \Omega, \mathbb{R}^{3\times 3})$ *and* $A(x,\omega)|_{D^-\times\Omega} \in C^1(D^- \times \Omega, \mathbb{R}^{3\times 3})$.
4. *The doping concentration* $C_{\mathrm{dop}}(x,\omega)$ *is bounded above and below with the bounds*

$$\underline{C} := \inf_{x\in D} C_{\mathrm{dop}}(x,\omega) \le C_{\mathrm{dop}}(x,\omega) \le \sup_{x\in D} C_{\mathrm{dop}}(x,\omega) =: \overline{C} \quad \forall \omega \in \Omega.$$

5. *There is a constant* $\mathbb{R} \ni K \ge 1$ *satisfying*

$$\frac{1}{K} \le u_D(x), v_D(x) \le K \quad \forall x \in \partial D_{\mathrm{Si},D}.$$

6. *The functionals* $M_\alpha : L^2(\Omega; H^1(D)) \cap L^\infty(D\times\Omega) \to L^2(\Omega; H^{1/2}(\Gamma)) \cap L^\infty(\Gamma\times\Omega)$ *and* $M_\gamma : L^2(\Omega; H^1(D)) \cap L^\infty(D\times\Omega) \to L^\infty(\Gamma\times\Omega)$ *are continuous.*
7. *The mobilities* $\mu_n(x,\omega)$ *and* $\mu_p(x,\omega)$ *are uniformly bounded functions of* $x \in D$ *and* $\omega \in \Omega$*, i.e.,*

$$\begin{aligned} 0 < \mu_n^- \le \mu_n(x,\omega) \le \mu_n^+ < \infty \qquad & \forall x \in D, \quad \forall \omega \in \Omega, \\ 0 < \mu_p^- \le \mu_p(x,\omega) \le \mu_p^+ < \infty \qquad & \forall x \in D, \quad \forall \omega \in \Omega, \end{aligned}$$

where $\mu_p(x,\omega), \mu_n(x,\omega) \in C^1(D_{\mathrm{Si}} \times \Omega, \mathbb{R}^{3\times 3})$.
Furthermore, the inclusions $f(x,\omega) \in L^2(\Omega; L^2(D)) \cap L^\infty(D\times\Omega)$*,* $V_D(x) \in H^{1/2}(\partial D) \cap L^\infty(\Gamma)$*,* $u_D, v_D(x) \in H^{1/2}(\partial D_{\mathrm{Si}})$*,* $\alpha(x,\omega) \in L^2(\Omega; H^{1/2}(\Gamma))$*, and* $\gamma(x,\omega) \in L^2(\Omega; L^2(\Gamma))$ *hold.*

Assumptions 3 and 7 guarantee the uniform ellipticity of the Poisson and the continuity equations, respectively.

3.2. Weak Solution of the Model Equations

In order to define the weak formulation of the stochastic boundary-value problem (2), it suffices to consider the semilinear boundary-value problem

$$-\nabla\cdot(A(x,\omega)\nabla w(x,\omega)) + h(x,w(x,\omega)) = f(x,\omega) \quad \forall x \in D\setminus\Gamma \quad \forall \omega \in \Omega, \tag{3a}$$
$$w(x,\omega) = w_D(x) \quad \forall x \in \partial D_D \quad \forall \omega \in \Omega, \tag{3b}$$
$$\mathbf{n}\cdot\nabla w(x,\omega) = 0 \quad \forall x \in \partial D_N \quad \forall \omega \in \Omega, \tag{3c}$$
$$w(0+,y,\omega) - w(0-,y,\omega) = \alpha(y,\omega) \quad \forall x \in \Gamma \quad \forall \omega \in \Omega, \tag{3d}$$
$$A(0+)\partial_x w(0+,y,\omega) - A(0-)\partial_x w(0-,y,\omega) = \gamma(y,\omega) \quad \forall x \in \Gamma \quad \forall \omega \in \Omega, \tag{3e}$$

which is a semilinear Poisson equation with interface conditions. The coefficient A here is either equal to A or equal to $\mu_n e^{V/U_T}$ or $\mu_p e^{-V/U_T}$ in (2). However, uniform ellipticity holds in each of these cases per Assumption 1.

For the weak formulation, we define the Hilbert space

$$X := H^1_g(D) = \left\{ w \in H^1(D) \mid Tw = g \right\} \tag{4}$$

as the solution space, where T is the trace operator defined such that $Tw = g$, where g is Dirichlet lift of $w_D := w|_{\partial D_D}$. The operator T is well-defined and continuous from $H^1(D)$ onto $H^{1/2}(\partial D)$ for the Lipschitz domain D. For $g = 0$, we define the test space

$$X_0 := H^1_0(D) = \left\{ w \in H^1(D) \mid Tw = 0 \right\}. \tag{5}$$

Definition 3.1 (Bochner spaces)**.** Given a Banach space $(X, \|\cdot\|_X)$ and $1 \le p \le +\infty$, the *Bochner space* $L^p(\Omega; X)$ is defined to be the space of all measurable functions $w\colon \Omega \to X$ such that for every $\omega \in \Omega$ the norm

$$\|w\|_{L^p(\Omega;X)} := \begin{cases} \Big(\int_\Omega \|w(\cdot,\omega)\|_X^p \mathrm{d}\mathbb{P}(\omega) \Big)^{1/p} = \mathbb{E}\Big[\|w(\cdot,\omega)\|_X^p\Big]^{1/p} < \infty, & 1 \le p < \infty, \\ \operatorname{ess\,sup}_{\omega\in\Omega} \|w(\cdot,\omega)\|_X < \infty, & p = \infty \end{cases} \tag{6}$$

is finite.

To derive the variational formulation of our model (3), we fix the event $\omega \in \Omega$ at first, multiply (3a) by a test function $\phi \in L^2(\Omega; X_0)$, and integrate by parts in D to obtain the relation

$$\int_D A\nabla w \cdot \nabla\phi + \int_D h(w)\phi = \int_D f\phi + \int_\Gamma \gamma\phi \qquad \forall \phi \in L^2(\Omega; X_0).$$

Definition 3.2 (Weak solution on $D \times \Omega$)**.** Suppose that A satisfies Assumptions 1 and that $f(x,\omega) \in L^2(\Omega; L^2(D))$, $w_D(x) \in H^{1/2}(\partial D_D)$, and $\gamma(x,\omega) \in L^2(\Omega; L^2(\Gamma))$ holds. A function $w \in L^2(\Omega; X)$ is called a *weak solution* of the boundary-value problem (3), if it satisfies

$$a(w,\phi) = \ell(\phi) \qquad \forall \phi \in L^2(\Omega; X_0), \tag{7}$$

where $a\colon L^2(\Omega; X) \times L^2(\Omega; X_0) \to \mathbb{R}$ and $\ell\colon L^2(\Omega; X_0) \to \mathbb{R}$ are defined by

$$a(w,\phi) := \mathbb{E}\left[\int_D A\nabla w \cdot \nabla\phi \mathrm{d}x\right] + \mathbb{E}\left[\int_D h\,(w)\,\phi \mathrm{d}x\right]$$

and

$$\ell(\phi) := \mathbb{E}\left[\int_D f\phi \mathrm{d}x\right] + \mathbb{E}\left[\int_\Gamma \gamma\phi \mathrm{d}x\right].$$

3.3. Existence and Local Uniqueness of the Solution

In the next step, we prove existence and local uniqueness of solutions of system of stochastic elliptic boundary-value problems with interface conditions (2) using the Schauder fixed-point theorem and the implicit-function theorem similarly to [2, Theorem 2.2 and 5.2].

Theorem 1 (Existence)**.** *Under Assumptions 1, for every $f(x,\omega) \in L^2(\Omega; L^2(D))$ and $V_D, u_D, v_D \in H^{1/2}(\partial D)$, there exists a weak solution*

$$\begin{aligned}(V(x,\omega), u(x,\omega), v(x,\omega), \alpha(x,\omega), \gamma(x,\omega)) \in\ & (L^2(\Omega; H^1_{V_D}(D) \cap L^\infty(D\times\Omega)) \\ & \times (L^2(\Omega; H^1_{u_D}(D_{\mathrm{Si}})) \cap L^\infty(D_{\mathrm{Si}}\times\Omega)) \times (L^2(\Omega; H^1_{v_D}(D_{\mathrm{Si}})) \cap L^\infty(D_{\mathrm{Si}}\times\Omega)) \\ & \times (L^2(\Omega; H^1(\Gamma)) \cap L^\infty(\Gamma\times\Omega))^2\end{aligned}$$

of the stochastic boundary-value problem (2), and for every $\omega \in \Omega$ it satisfies the L^∞-estimate

$$\begin{aligned} \underline{V} \le V(x,\omega) \le \overline{V} \qquad & \text{in } D, \\ \frac{1}{K} \le u(x,\omega) \le K \qquad & \text{in } D_{\mathrm{Si}}, \\ \frac{1}{K} \le v(x,\omega) \le K \qquad & \text{in } D_{\mathrm{Si}}, \end{aligned}$$

where

$$\begin{aligned} \underline{V} &:= \min(\inf_{\partial D_D} V_D, \Phi - \sup_D V_L, U_T \ln(\frac{1}{2Kn_i}(\underline{C} + \sqrt{\underline{C}^2 + 4n_i^2})) - \sup_D V_L), \\ \overline{V} &:= \max(\sup_{\partial D_D} V_D, \Phi - \inf_D V_L, U_T \ln(\frac{K}{2n_i}(\overline{C} + \sqrt{\overline{C}^2 + 4n_i^2})) - \inf_D V_L). \end{aligned}$$

Here $V_L(x,\omega)$ is the solution of the linear problem (i.e., problem (3) *with $h \equiv 0$), for which the estimate*

$$\|V_L\|_{L^2(\Omega;H^1_{V_D}(D))} \le C\left(\|f\|_{L^2(\Omega;L^2(D))} + \|V_D\|_{H^{1/2}(\partial D_D)} + \|\alpha\|_{L^2(\Omega;H^{1/2}(\Gamma))} + \|\gamma\|_{L^2(\Omega;L^2(\Gamma))}\right)$$

holds, where C is a positive constant.

Proof. The existence of the solution is proved using the Schauder fixed-point theorem and the estimates are obtained from a maximum principle. First, we define a suitable space

$$\begin{aligned} N := \{(V,u,v,\alpha,\gamma) \in L^2(\Omega;H^1(D)) \times L^2(\Omega;H^1(D_{\mathrm{Si}}))^2 \times L^2(\Omega;H^1(\Gamma))^2 \;\big|\; \\ \underline{V} \le V(x,\omega) \le \overline{V} \quad \text{a.e. in } D\times\Omega, \quad \frac{1}{K} \le u(x,\omega), v(x,\omega) \le K \quad \text{a.e. in } D_{\mathrm{Si}}\times\Omega, \\ \alpha,\gamma \text{ bounded a.e. on } \Gamma\times\Omega\}, \end{aligned}$$

which is closed and convex. Then we define a fixed-point map $F\colon N \to N$ by

$$F(V_0,u_0,v_0,\alpha_0,\gamma_0) := (V_1,u_1,v_1,\alpha_1,\gamma_1),$$

where the elements of the vector $(V_1,u_1,v_1,\alpha_1,\gamma_1)$ are the solutions of the following equations for given data $(V_0,u_0,v_0,\alpha_0,\gamma_0)$.

1. Solve the elliptic equation

$$\begin{aligned} -\nabla\cdot(A\nabla V_1) &= qn_i(e^{-V_1/U_T}v_0 - e^{V_1/U_T}u_0) + qC_{\mathrm{dop}} && \text{in } D,\\ \mathbf{n}\cdot\nabla V_1 &= 0 && \text{on } \partial D_N,\\ V_1 &= V_D && \text{on } \partial D_D \end{aligned}$$

   for V_1.
2. Solve the elliptic equation

$$\begin{aligned} U_T\nabla\cdot(\mu_n e^{V_1/U_T}\nabla u_1) & \\ -\frac{u_1v_0-1}{\tau_p(e^{V_1/U_T}u_0+1)+\tau_n(e^{-V_1/U_T}v_0+1)} &= 0 \quad \text{in } D_{\mathrm{Si}},\\ \mathbf{n}\cdot\nabla u_1 &= 0 \quad \text{on } \partial D_{\mathrm{Si},N},\\ u_1 &= u_D \ \text{ on } \partial D_{\mathrm{Si},D} \end{aligned}$$

   for u_1.
3. Solve the elliptic equation

$$\begin{aligned} U_T\nabla\cdot(\mu_p e^{-V_1/U_T}\nabla v_1) & \\ -\frac{u_0v_1-1}{\tau_p(e^{V_1/U_T}u_0+1)+\tau_n(e^{-V_1/U_T}v_0+1)} &= 0 \quad \text{in } D_{\mathrm{Si}}\\ \mathbf{n}\cdot\nabla v_1 &= 0 \quad \text{on } \partial D_{\mathrm{Si},N},\\ v_1 &= v_D \ \text{ on } \partial D_{\mathrm{Si},D}, \end{aligned}$$

   for v_1.
4. Update the surface-charge density and dipole-moment density according to the microscopic model

$$\begin{aligned} \alpha_1(y,\omega) &:= M_\alpha(V_0),\\ \gamma_1(y,\omega) &:= M_\gamma(V_0). \end{aligned}$$

Using Lemmata on the existence and uniqueness of solutions of elliptic boundary-value problems with interface conditions, every equation present in the model is uniquely solvable. Therefore the map F is well-defined. Furthermore, continuity and the self-mapping property of F as well as the precompactness of $F(N)$ can be shown similarly to [2, Theorem 2.2] and [22, Theorem 1]. Therefore, applying the Schauder fixed-point theorem yields a fixed-point of F, which is a weak solution of (2). □

In general, the solution in Theorem 1 is not unique; uniqueness of the solution only holds in a neighborhood around thermal equilibrium. This necessitates sufficiently small Dirichlet boundary conditions. The following theorem yields local uniqueness of the solution of our system (2) of model equation. The proof is based on the implicit-function theorem.

Theorem 2 (Local uniqueness)**.** *Under Assumption 1, for every $f(x,\omega) \in L^2(\Omega; L^2(D))$, $V_D, u_D, v_D \in H^{1/2}(\partial D)$, $\alpha \in L^2(\Omega; H^{1/2}(\Gamma))$, and $\gamma \in L^2(\Omega; L^2(\Gamma))$, there exists a sufficiently small $\sigma \in \mathbb{R}$ with $|U| < \sigma$ such that the stochastic problem in the existence theorem 1 has a locally unique solution*

$$\begin{aligned}\Big(V^*(U), u^*(U), v^*(U), \alpha^*(U), \gamma^*(U)\Big) \in\ & L^2(\Omega; H^2(D \setminus \Gamma)) \times L^2(\Omega; H^2(D_{\mathrm{Si}}))^2 \\ & \times L^2(\Omega; H^{1/2}(\Gamma)) \times L^2(\Omega; L^2(\Gamma)).\end{aligned}$$

The solution satisfies

$$\Big(V^*(0), u^*(0), v^*(0), \alpha^*(0), \gamma^*(0)\Big) = (V_e, 1, 1, \alpha_e, \gamma_e)$$

and it depends continuously differentiably on U as a map from $\{U \in \mathbb{R}^k,\ |U| < \sigma\}$ into $L^2(\Omega; H^2(D \setminus \Gamma)) \times L^2(\Omega; H^2(D_{\mathrm{Si}}))^2 \times L^2(\Omega; H^{1/2}(\Gamma)) \times L^2(\Omega; L^2(\Gamma))$.

Proof. We call the equilibrium potential $V_e(x,\omega)$ and the equilibrium surface densities $\alpha_e(x,\omega)$ and $\gamma_e(x,\omega)$. $(V_e, 1, 1, \alpha_e, \gamma_e)$ is a solution of the stochastic equilibrium boundary-value problem, which has a unique solution due to the existence and uniqueness of solutions of stochastic semilinear elliptic boundary-value problems of the form

$$\begin{aligned}
-\nabla \cdot (A(x,\omega)\nabla V_e(x,\omega)) &= qC_{\mathrm{dop}}(x,\omega) - qn_i(e^{V_e(x,\omega)/U_T} - e^{-V_e(x,\omega)/U_T}) && \text{in } D_{\mathrm{Si}},\\
-\nabla \cdot (A(x,\omega)\nabla V_e(x,\omega)) &= 0 && \text{in } D_{\mathrm{ox}},\\
-\nabla \cdot (A(x,\omega)\nabla V_e(x,\omega)) &= -2\eta \sinh(\beta(V_e(x,\omega) - \Phi(x,\omega))) && \text{in } D_{\mathrm{liq}},\\
V_e(0+,y,\omega) - V_e(0-,y,\omega) &= \alpha_e(y,\omega) && \text{on } \Gamma,\\
A(0+)\partial_x V_e(0+,y,\omega) - A(0-)\partial_x V_e(0-,y,\omega) &= \gamma_e(y,\omega) && \text{on } \Gamma,\\
V_e(x,\omega) &= V_D(x) && \text{on } \partial D_D,\\
\mathbf{n} \cdot \nabla V_e(x,\omega) &= 0 && \text{on } \partial D_N.
\end{aligned}$$

To apply the implicit-function theorem, we define the map

$$\begin{aligned}&G\colon B \times S_{\sigma_1(0)} \to L^2(\Omega; L^2(D)) \times L^2(\Omega; L^2(D_{\mathrm{Si}}))^2 \times L^2(\Omega; L^2(\Gamma))^2,\\ &G(V,u,v,\alpha,\gamma,U) = 0,\end{aligned}$$

where G is given by the boundary-value problem (2) after substituting $\overline{V} := V - V_D(U)$, $\overline{u} := u - u_D(U)$, and $\overline{v} := v - v_D(U)$. B is an open subset of $L^2(\Omega; H^2_\partial(D)) \times L^2(\Omega; H^2_\partial(D_{\mathrm{Si}}))^2 \times L^2(\Omega; L^2(\Gamma))^2$ with

$$H^2_\partial(D) := \{\phi \in H^2(D) \mid \mathbf{n} \cdot \nabla\phi = 0 \text{ on } \partial D_N,\ \phi = 0 \text{ on } \partial D_D\},$$

and the sphere S_{σ_1} with radius σ_1 and center 0 is a subset of $\mathbb{R}^d$. The equilibrium solution $(V_e - V_D(0), 0, 0, \alpha_e, \gamma_e, 0)$ is a solution of the equation $G = 0$. One can show that the Fréchet derivative $D_{(V,u,v,\alpha,\gamma)}G(V_e - V_D(0), 0, 0, \alpha_e, \gamma_e, 0)$ has a bounded inverse (see, e.g., [2, Theorem 2.2]). Then the implicit-function theorem implies uniqueness of the solution of (2). □

4. Multi-Level Monte-Carlo Finite-Element Method

We start by briefly recapitulating the finite-element approximation of the system of model equations considered here. Then we review the types of error in the Monte-Carlo approximation of solutions of stochastic partial differential equations in Section 4.2. In Section 4.3, a multi-level Monte-Carlo (MLMC) finite-element (FE) method for the solution of the system of stochastic equations (2) is developed. We give an error bound for MLMC-FEM approximation and discuss the computational complexity.

4.1. The Finite-Element Method

In this subsection, we briefly recapitulate the Galerkin finite-element approximation and fix some notation. It provides the foundation for the following section.

We suppose that the domain D can be partitioned into quasi-uniform triangles or tetrahedra such that sequences $\{\tau_{h_\ell}\}_{\ell=0}^{\infty}$ of regular meshes are obtained. For any $\ell \geq 0$, we denote the mesh size of τ_{h_ℓ} by

$$h_\ell := \max_{K \in \tau_{h_\ell}} \{\operatorname{diam} K\}.$$

To ensure that the mesh quality does not deteriorate as refinements are made, shape-regular meshes can be used.

Definition 4.1 (Shape regular mesh)**.** A sequence $\{\tau_{h_\ell}\}_{l=0}^{\infty}$ of meshes is *shape regular* if there exists a constant $\kappa < \infty$ independent of ℓ such that

$$\frac{h_K}{\rho_K} \geq \kappa \quad \forall K \in \tau_{h_\ell}.$$

Here ρ_K is the radius of the largest ball that can be inscribed into any $K \in \tau_{h_\ell}$.

Uniform refinement of the mesh can be achieved by regular subdivision. This results in the mesh size

$$h_\ell = r^{-\ell} h_0, \tag{8}$$

where h_0 denotes the mesh size of the coarsest triangulation and $r > 1$ is independent of ℓ. The nested family $\{\tau_{h_\ell}\}_{\ell=0}^{\infty}$ of regular triangulations obtained in this way is shape regular.

The Galerkin approximation is the discrete version of the weak formulation in (7) of the stochastic elliptic boundary-value problem (2). We consider finite-element discretizations with approximations $u_h \in X_{h_\ell}$ of $u \in X$. Given a mesh τ_{h_ℓ}, X is the solution space (4) and $X_{h_\ell} \subset X$ is the discretized space. For all $k \geq 1$, it is defined as

$$X_{h_\ell} := \mathbb{P}^k(\tau_{h_\ell}) := \{u \in X \mid u|_K \in \mathbb{P}^k(K) \ \ \forall K \in \tau_{h_\ell}\}, \tag{9}$$

where $\mathbb{P}^k(K) := \operatorname{span}\{x^\alpha \mid |\alpha| \leq k\}$ is the space of polynomials of total degree less equal k. The space X_0 is the space (5) of test functions. The discretized test space $X_{0h_\ell} \subset X_0$ is defined analogously to (9).

After introducing the finite-element spaces, everything is ready to define the Galerkin approximation.

Definition 4.2 (Galerkin approximation)**.** Suppose $X_{h_\ell} \subset X$ and $X_{0h_\ell} \subset X_0$. The *Galerkin approximation* of (3) is the function

$$w_{h_\ell} \in L^2(\Omega; X_{h_\ell})$$

that satisfies

$$B(w_{h_\ell}, \phi_{h_\ell}) = F(\phi_{h_\ell}) \qquad \forall \phi_{h_\ell} \in L^2(\Omega; X_{0h_\ell}), \tag{10}$$

where B and F are defined in (7).

4.2. Monte-Carlo Finite-Element Approximation

The straightforward Monte-Carlo method for a stochastic PDE approximates the expectation $\mathbb{E}[u]$ of the solution u by the sample mean of a (large) number of evaluations. Since we use the same finite-element mesh τ with the mesh size h for all samples, we drop the index ℓ in this subsection for the MC-FEM. We approximate $\mathbb{E}[u]$ by $\mathbb{E}[u_h]$, where u_h is again the FE approximation of u using a mesh of size h. The standard MC estimator E_{MC} for $\mathbb{E}[u_h]$ is the sample mean

$$\mathrm{E}_{\mathrm{MC}}[u_h] := \hat{u}_h := \frac{1}{M} \sum_{i=1}^{M} u_h^{(i)}. \tag{11}$$

where $u_h^{(i)} = u_h(x, \omega^{(i)})$ is the ith sample of the solution.

The following lemma shows the error of the MC estimator for a random variable u which is not descretized in space is of order $O(M^{-1/2})$.

Lemma 3. *For any number of samples $M \in \mathbb{N}$ and for a random variable $u \in L^2(\Omega; X)$, the inequality*

$$\|\mathbb{E}[u] - \mathrm{E}_{\mathrm{MC}}[u]\|_{L^2(\Omega;X)} = M^{-1/2}\sigma[u] \tag{12}$$

holds for the MC error, where $\sigma[u] := \|\mathbb{E}[u] - u\|_{L^2(\Omega;X)}$.

Proof. The result follows from the calculation

$$\begin{aligned}
\|\mathbb{E}[u] - \mathrm{E}_{\mathrm{MC}}[u]\|^2_{L^2(\Omega;X)} &= \mathbb{E}\Big[\Big\|\mathbb{E}[u] - \frac{1}{M}\sum_{i=1}^{M} u^{(i)}\Big\|_X^2\Big] \\
&= \frac{1}{M^2}\sum_{i=1}^{M}\mathbb{E}\Big[\|\mathbb{E}[u] - u^{(i)}\|_X^2\Big] \\
&= \frac{1}{M}\mathbb{E}\Big[\|\mathbb{E}[u] - u\|_X^2\Big] = M^{-1}\sigma^2[u].
\end{aligned}$$

□

Next we generalize the result to the finite-element solution by using the MC estimator to approximate the expectation $\mathbb{E}[u]$ of a solution u of an SPDE, which is descretized in space by the finite-element method. In other words, if u_h and $\hat{u}_h$ are the finite-element and MC solutions of the SPDE, respectively, then we have

$$\mathbb{E}[u] \approx \mathbb{E}[u_h] \approx \hat{u}_h.$$

Therefore, the MC-FEM method involves two approximations and hence there are two sources of error.

Discretization error The approximation of $\mathbb{E}[u]$ by $\mathbb{E}[u_h]$ gives to the discretization error, which stems from the spatial discretization.

Statistical error The approximation of the expected value $\mathbb{E}[u_h]$ by the sample mean $\hat{u}_h$ gives rise to the statistical error, which is caused by the MC estimator.

Lemma 3 takes care of the statistical error. The order of the discretization error depends on the order of the finite-element method.

Proposition 1. *Suppose $\alpha, C_0, C_1 \in \mathbb{R}^+$. Let $\mathrm{E}_{\mathrm{MC}}[u_h]$ be the Monte-Carlo estimator with M samples to approximate the expectation $\mathbb{E}[u]$ of a solution $u(\cdot,\omega) \in X$ of an SPDE by using a FE solution $u_h(\cdot,\omega) \in X_h$ with mesh size h. Suppose that the discretization error converges with order α, i.e.,*

$$\|\mathbb{E}[u - u_h]\|_X \leq C_1 h^\alpha, \tag{13}$$

and that the estimate

$$\sigma[u_h] \leq C_0 \tag{14}$$

holds. Then the error of the MC estimator satisfies

$$\|\mathbb{E}[u] - \mathrm{E}_{\mathrm{MC}}[u_h]\|_{L^2(\Omega;X)} = O(h^\alpha) + O(M^{-1/2}). \tag{15}$$

Proof. We use the root mean square error (RMSE) to measure the accuracy of the total approximation and analyze the contribution of both errors. Using the triangle inequality and Lemma (3), we find

$$\begin{aligned}
\mathrm{RMSE} &:= \|\mathbb{E}[u] - \mathrm{E}_{\mathrm{MC}}[u_h]\|_{L^2(\Omega;X)} \\
&\leq \|\mathbb{E}[u] - \mathbb{E}[u_h]\|_X + \|\mathbb{E}[u_h] - \mathrm{E}_{\mathrm{MC}}[u_h]\|_{L^2(\Omega;X)} \\
&\leq \|\mathbb{E}[u - u_h]\|_X + M^{-1/2}\sigma[u_h] \\
&\leq C_1 h^\alpha + C_0 M^{-1/2} \\
&= O(h^\alpha) + O(M^{-1/2}).
\end{aligned} \tag{16}$$

The last expressions are obtained by using the assumtions (13) and (14). □

4.3. Multi-Level Monte-Carlo Finite-Element Approximation

In this section, we first present the MLMC FE method and an its error. In this method, several levels of meshes are used and the MC estimator is employed to approximate the solution on each level independently. We start by discretizing the variational formulation (7) on the sequence

$$X_{h_0} \subset X_{h_1} \subset \cdots \subset X_{h_L} \subset X$$

of finite-dimensional sub-spaces, where $X_{h_\ell} := \mathbb{P}^1(\tau_{h_\ell})$ for all $\ell \in \{0, 1, 2, \ldots, L\}$ (see Section 4.1). The finite-element approximation at level L can be written as the telescopic sum

$$u_{h_L} = u_{h_0} + \sum_{\ell=1}^{L} (u_{h_\ell} - u_{h_{\ell-1}}),$$

where each u_{h_ℓ} is the solution on the mesh τ_{h_ℓ} at level ℓ. Therefore, the expected value of u_{h_L} is given by

$$\mathbb{E}[u_{h_L}] = \mathbb{E}[u_{h_0}] + \mathbb{E}\left[\sum_{\ell=1}^{L} (u_{h_\ell} - u_{h_{\ell-1}})\right] = \mathbb{E}[u_{h_0}] + \sum_{\ell=1}^{L} \mathbb{E}[u_{h_\ell} - u_{h_{\ell-1}}]. \tag{17}$$

In the MLMC FEM, we estimate $\mathbb{E}[u_{h_\ell} - u_{h_{\ell-1}}]$ by a level dependent number M_ℓ of samples. The MLMC estimator $\mathbb{E}[u]$ is defined as

$$\mathrm{E}_{\mathrm{MLMC}}[u] := \hat{u}_{h_L} := \mathrm{E}_{\mathrm{MC}}[u_{h_0}] + \sum_{\ell=1}^{L} \mathrm{E}_{\mathrm{MC}}[u_{h_\ell} - u_{h_{\ell-1}}], \tag{18}$$

where E_{MC} is the Monte-Carlo estimator defined in (11). Therefore, we find

$$\hat{u}_{h_L} = \frac{1}{M_0} \sum_{i=1}^{M_0} u_{h_0}^{(i)} + \sum_{\ell=1}^{L} \frac{1}{M_\ell} \sum_{i=1}^{M_\ell} (u_{h_\ell}^{(i)} - u_{h_{\ell-1}}^{(i)}). \tag{19}$$

It is important to note that the approximate solutions $u_{h_\ell}^{(i)}$ and $u_{h_{\ell-1}}^{(i)}$ correspond to the same sample i, but are computed on different levels of the mesh, i.e., on the meshes M_ℓ and $M_{\ell-1}$, respectively.

Recalling the two sources of error constituting the MC-FE error, the following result holds for the MLMC-FEM error.

Proposition 2. *Suppose $\alpha, \beta, C_0, C_1 \in \mathbb{R}^+$. Let $\mathrm{E}_{\mathrm{MLMC}}[u_{h_L}]$ be the multi-level Monte-Carlo estimator to approximate the expectation $\mathbb{E}[u]$ of a solution $u(\cdot, \omega) \in X$ of an SPDE by using a FE solution $u_{h_\ell}(\cdot, \omega) \in X_{h_\ell}$ with M_ℓ samples in level ℓ, $\ell \in \{0, 1, 2, \ldots, L\}$ and with mesh size h_ℓ. Suppose that the convergence order α for the discretization error, i.e.,*

$$\|\mathbb{E}[u - u_{h_\ell}]\|_X \leq C_1 h_\ell^\alpha, \tag{20}$$

the convergence order β for

$$\sigma[u_{h_\ell} - u_{h_{\ell-1}}] \leq C_0 h_{\ell-1}^\beta, \tag{21}$$

and assume that the estimate

$$\sigma[u_{h_0}] \leq C_{00} \tag{22}$$

holds, where $\sigma[u] := \|\mathbb{E}[u] - u\|_{L^2(\Omega;X)}$. Then the error of the MLMC estimator satisfies

$$\|\mathbb{E}[u] - \mathrm{E}_{\mathrm{MLMC}}[u_{h_L}]\|_{L^2(\Omega;X)} = O(h_L^\alpha) + O(M_0^{-1/2}) + \sum_{\ell=1}^{L} O(M_\ell^{-1/2}) O(h_{\ell-1}^\beta). \tag{23}$$

Proof. Similarly to the MC estimator, the RMSE assesses the accuracy of the MLMC FE estimator. Using the triangle inequality and the relations (17) and (18), we find

$$\begin{aligned}
\mathrm{RMSE} &:= \|\mathbb{E}[u] - \mathrm{E}_{\mathrm{MLMC}}[u_{h_L}]\|_{L^2(\Omega;X)} \\
&\leq \|\mathbb{E}[u] - \mathbb{E}[u_{h_L}]\|_X + \|\mathbb{E}[u_{h_L}] - \mathrm{E}_{\mathrm{MLMC}}[u_{h_L}]\|_{L^2(\Omega;X)} \\
&\leq \|\mathbb{E}[u - u_{h_L}]\|_X + \|\mathbb{E}[u_{h_0}] - \mathrm{E}_{\mathrm{MC}}[u_{h_0}]\|_{L^2(\Omega;X)} \\
&\quad + \sum_{\ell=1}^{L} \|\mathbb{E}[u_{h_\ell} - u_{h_{\ell-1}}] - \mathrm{E}_{\mathrm{MC}}[u_{h_\ell} - u_{h_{\ell-1}}]\|_{L^2(\Omega;X)}.
\end{aligned}$$

Next we apply the assumptions (20)–(22) and Lemma 3 to obtain the asserted orders for the error by calculating

$$\begin{aligned}
\mathrm{RMSE} &\leq \|\mathbb{E}[u - u_{h_L}]\|_X + M_0^{-1/2}\sigma[u_{h_0}] \\
&\quad + \sum_{\ell=1}^{L} M_\ell^{-1/2}\sigma[u_{h_\ell} - u_{h_{\ell-1}}] \\
&\leq C_1 h_L^\alpha + C_{00} M_0^{-1/2} + C_0 \sum_{\ell=1}^{L} M_\ell^{-1/2} h_{\ell-1}^\beta \\
&= O(h_L^\alpha) + O(M_0^{-1/2}) + \sum_{\ell=1}^{L} O(M_\ell^{-1/2}) O(h_{\ell-1}^\beta).
\end{aligned} \tag{24}$$

This concludes the proof. □

5. Optimal Monte-Carlo and Multi-Level Monte-Carlo Methods

In this section, we first estimate the computational cost of the MLMC FE method to achieve a given accuracy and compare it with the MC FE method. Based on these considerations, the computational work is then minimized for a given accuracy to be achieved in order to find the optimal number of samples and the optimal mesh size.

As the model equations (2) are a system of PDEs, the work estimate consists of the sum of the work for all equations, i.e., the Poisson equation for V and the two drift-diffusion equations for u and v. Therefore, the total computational work is given by

$$W := W_P + 2W_D = W_{P,a} + W_{P,s} + 2W_{D,a} + 2W_{D,s}, \tag{25}$$

where the index P indicates the Poisson equation, the index D indicates the two drift-diffusion equations, the index a denotes assembly of the system matrix, and the index s denotes solving the system matrix. We assume that the necessary number of fixed-point or Newton iterations to achieve numerical convergence is constant; this is supported by the numerical results.

For each of these four parts the work in level ℓ is given by

$$(W_\ell)_{P,a} = \mu_1 M_\ell h_\ell^{-\gamma_1}, \tag{26a}$$

$$(W_\ell)_{P,s} = \mu_2 M_\ell h_\ell^{-\gamma_2}, \tag{26b}$$

$$(W_\ell)_{D,a} = \mu_3 M_\ell h_\ell^{-\gamma_3}, \tag{26c}$$

$$(W_\ell)_{D,s} = \mu_4 M_\ell h_\ell^{-\gamma_4} \tag{26d}$$

with all $\mu_k > 0$ and $\gamma_k > 0$. Here M_ℓ is the number of samples used at level ℓ, and h_ℓ is the corresponding mesh size.

Analogously, in the case of the vanilla Monte-Carlo method, the computational work is obtained without stratification, i.e., there is only one level. In this case, we will drop the index ℓ.

The exponents (and constants) in equations (26) are determined by the algorithm used for assembling the FE matrix in the case of $W_{P,a}$ and $W_{D,a}$ (see, e.g., [23] for an efficient algorithm) and by the order of the FE discretization in the case of $W_{P,s}$ and $W_{D,s}$ (see Section 4.2). The constants $\mu_i > 0$ depend on the implementation.

5.1. The Optimal Monte-Carlo Finite-Element Method

In the case of the Monte-Carlo method, there is only one level so that the index ℓ will be dropped. We will choose the optimal M and h such that the total computational cost W is minimized given an error bound ϵ to be achieved. This optimization problem with inequality constraints can be solved using the Karush-Kuhn-Tucker (KKT) conditions, which are generalization of Lagrange multipliers in the presence of inequality constraints.

In view of (26) and (16), the most general problem is the following. We minimize the computational work subject to the accuracy constraint RMSE $\leq \varepsilon$, i.e., we solve the optimization problem

$$\begin{aligned} \underset{M,h}{\text{minimize}} \quad & f(M,h) := \sum_{k=1}^{N} \mu_k M h^{-\gamma_k} \\ \text{subject to} \quad & g_1(M,h) := \varepsilon - \frac{C_0}{\sqrt{M}} - C_1 h^{\alpha} \geq 0, \\ & g_2(M) := M - 1 \geq 0, \\ & g_3(h) := h - \xi \geq 0. \end{aligned} \tag{27}$$

Here, $N \in \mathbb{N}$ and ξ is the smallest positive normalized floating-point number representable. Due to the exponents of h and M, it is a nonlinear constraint optimization problem. Our goal is to formulate the inequality constrained problem as an equality constrained problem to which Newton's method can be applied. In order to solve the optimization problem, we use the interior-point method [24, 25].

For each $\mu > 0$, we replace the non-negativity constraints with logarithmic barrier terms in the objective function

$$\begin{aligned} \underset{\chi,s}{\text{minimize}} \quad & f_\mu(\chi, s) := f(\chi) - \mu \sum_i \ln(s_i) \\ \text{subject to} \quad & g(\chi) - s = 0. \end{aligned} \tag{28}$$

Here χ, a vector, denotes (M, h) and the vectors g and s represent the $g_i(x)$ and s_i, respectively. The s_i are restricted to be positive away from zero to ensure that the $\ln(s_i)$ are bounded. As μ decreases to zero, the minimum of f_μ approaches the minimum of f. After denoting the Lagrange multiplier for the system (28) by y, the system

$$\begin{aligned} \nabla f(\chi) - \nabla g(\chi)^T y &= 0, \\ S Y e &= \mu e, \\ g(\chi) - s &= 0 \end{aligned}$$

is obtained, where S is a diagonal matrix with elements s_i, e is a vector of all ones, and ∇g denotes the Jacobian of the constraint g. Now we apply Newton's method to compute the search directions $\Delta\chi$, Δs, Δh via

$$\begin{pmatrix} H(\chi, y) & 0 & -A(\chi)^T \\ 0 & Y & S \\ A(x) & -I & 0 \end{pmatrix} \begin{pmatrix} \Delta\chi \\ \Delta s \\ \Delta h \end{pmatrix} = \begin{pmatrix} -\nabla f(\chi) + A(\chi)^T y \\ \mu e - S Y e \\ -g(\chi) + s \end{pmatrix}. \tag{29}$$

The Hessian matrix is given by

$$H(\chi, y) = \nabla^2 f(\chi) - \sum_i y_i \nabla^2 g_i(\chi)$$

and $A(\chi)$ is the Jacobian matrix of the constraint (27). The second equation is used to calculate Δs. By substituting into the third equation, we obtain the reduced KKT system

$$\begin{pmatrix} -H(\chi, y) & A(\chi)^T \\ A(\chi) & S Y^{-1} \end{pmatrix} \begin{pmatrix} \Delta\chi \\ \Delta s \end{pmatrix} = \begin{pmatrix} \nabla f(\chi) - A(\chi)^T y \\ -h(\chi) + \mu Y^{-1} e \end{pmatrix}. \tag{30}$$

Now we use iteration to update the solutions by

$$\chi^{(k+1)} := \chi^{(k)} + \alpha^{(k)}\Delta\chi^{(k)},$$
$$s^{(k+1)} := s^{(k)} + \alpha^{(k)}\Delta s^{(k)},$$
$$y^{(k+1)} := y^{(k)} + \alpha^{(k)}\Delta y^{(k)},$$

where $(\chi^{(0)}, s^{(0)}, y^{(0)})$ is the initial guess and $\alpha^{(k)}$ is chosen to ensure both that $s^{(k+1)} > 0$ and the objective function

$$\Psi_{\upsilon,\mu}(\chi, s) = f_\mu(\chi, s) + \frac{\upsilon}{2}\|g(\chi) - s\|,$$

is sufficiently reduced [26]. The parameter υ may increase with the iteration number to force the solution toward feasibility.

5.2. The Optimal Multi-Level Monte-Carlo Finite-Element Method

For an optimal multi-level Monte-Carlo finite-element method, our goal is to determine the optimal hierarchies $(L, \{M_\ell\}_{\ell=0}^{L}, h_0, r)$ which minimize the computational work subject to the given accuracy constraint RMSE $\leq \varepsilon$. The optimal number L of levels is also unknown a priori. To this end, we solve the optimization problem

$$\begin{aligned}
\underset{M_\ell,h_0,r}{\text{minimize}} \quad & f(M_\ell, h_0, r, L) := \sum_{\ell=0}^{L}\sum_{k=1}^{N} \mu_k M_\ell h_0^{-\gamma_k} r^{\ell\gamma_k} \\
\text{subject to} \quad & g_1(M_\ell, h_0, r, L) := \varepsilon - \frac{C_{00}}{\sqrt{M_0}} - C_0 \sum_{\ell=1}^{L} \frac{1}{\sqrt{M_\ell}} h_0^{\beta} r^{-(\ell-1)\beta} - C_1 h_0^{\alpha} r^{-L\alpha} \geq 0, \\
& g_2(M_\ell) := M_\ell - 1 \geq 0, \qquad \ell = 0, \ldots, L, \\
& g_3(h_0) := h_0 - \xi \geq 0, \\
& g_4(r) := r - 1 \geq 0,
\end{aligned} \tag{31}$$

where $N \in \mathbb{N}$ and ξ is the smallest positive normalized floating-point number representable by the machine.

Similar to the vanilla Monte-Carlo case, we use the interior-point method to solve this nonlinear problem and optimize the hierarchies. In problems with two or three physical/spatial dimensions, the optimal determination of the mesh sizes h_ℓ is a crucial factor in the optimization problem specifically if the exponents γ_k are greater than 1.

There are two options: one is to choose the h_ℓ as a geometric progression according to (8). In this case, we solve the minimization problem (31). The other is to choose the mesh sizes h_ℓ freely such that they only satisfy the natural condition

$$h_0 \geq h_1 \geq h_2 \geq \cdots \geq h_L.$$

We will explore both options in Section 6.

In the second case, when the mesh sizes are freely chosen, we write them as

$$h_\ell := \frac{h_0}{r_\ell}, \qquad \ell = 1, \ldots, L,$$

where $r_\ell := \prod_{i=1}^{\ell} r_i$ with $r_i \geq 1$. It is clear that $r_L \geq r_{L-1} \ldots \geq r_1 \geq 1$. Hence, in (31), we may replace r by r_ℓ and then the optimization problem can be rewritten as

$$\begin{aligned}
\underset{M_\ell,h_0,r_\ell}{\text{minimize}} \quad & f(M_\ell, h_0, r_\ell, L) := \sum_{\ell=0}^{L}\sum_{k=1}^{N} \mu_k M_\ell h_0^{-\gamma_k} r_\ell^{\gamma_k} \\
\text{subject to} \quad & g_1(M_\ell, h_0, r_\ell, L) := \varepsilon - \frac{C_{00}}{\sqrt{M_0}} - C_0 \sum_{\ell=1}^{L} \frac{1}{\sqrt{M_\ell}} h_0^{\beta} r_{\ell-1}^{-\beta} - C_1 h_0^{\alpha} r_L^{-\alpha} \geq 0, \\
& g_2(M_\ell) := M_\ell - 1 \geq 0, \qquad \ell = 0, \ldots, L, \\
& g_3(h_0) := h_0 - \xi \geq 0, \\
& g_4 := r_i - 1 \geq 0, \quad 1 \leq i \leq \ell \quad \text{and} \quad \ell = 1, \ldots, L.
\end{aligned} \tag{32}$$

In the next section, we apply these two approaches to a MLMC FE method and discuss their efficiency.

6. Numerical Results

In this section, we present numerical results for the Monte-Carlo and multi-level Monte-Carlo methods for the drift-diffusion-Poisson system. We also investigate the choices of the FE mesh sizes on each level, namely as geometric progressions or freely chosen. The random coefficients in the drift-diffusion-Poisson system considered here stem from a real-world application, namely the effect of random dopants in nanoscale semiconductor devices, which is of great importance in its own right.

6.1. The Leading Example

Random-dopant effects are called discrete-dopant fluctuation effects [27, 28, 29]. In nanoscale semiconductor devices, the charge profile of the dopant atoms cannot be validly modeled as a continuum anymore, but the random location of each dopant needs to be taken into account. This means that each device is a realization of a random process and corresponds to an event ω. In this manner, the potential and carrier-density fluctuations due to the discreteness and randomness of the dopants are clearly captured.

Here the silicon lattice is doped with boron as the impurity atoms. The domain $D \subset \mathbb{R}^2$ is depicted in Figure 2. The thickness of the oxide layer is 8 nm, the thickness of the nanowire is 50 nm, and its width is 60 nm. Regarding the geometry, Dirichlet boundary conditions are used at the contacts with a back-gate voltage of -1 V (at the bottom of the device) and an electrode voltage of 0 V (at the top of the device). Zero Neumann boundary conditions are used everywhere else. The relative permittivities in the subdomains are $A_{\mathrm{Si}} = 11.7$, $A_{\mathrm{ox}} = 3.9$, $A_{\mathrm{liq}} = 78$, and $A_{\mathrm{dop}} = 4.2$. The number of dopants placed randomly in the device corresponds to a doping concentration of $10^{16}\,\mathrm{cm}^{-3}$. According to its volume, the silicon subdomain hence contains 6 negative impurity atoms when $C_{\mathrm{dop}} = 5 \cdot 10^{15}\,\mathrm{cm}^{-3}$ and 600 dopants when $C_{\mathrm{dop}} = 5 \cdot 10^{17}\,\mathrm{cm}^{-3}$.

In order to solve the system of equations, we use Scharfetter-Gummel iteration. In spite of the quadratic convergence of Newton's method for the system, Scharfetter-Gummel iteration has advantages for the problem at hand. First of all, Scharfetter-Gummel iteration is much less sensitive to the choice of the initial guess than Newton's method. Another important feature is the reduced computational effort and memory requirement, since in each iteration it requires the successive solution of three much smaller elliptic problems.

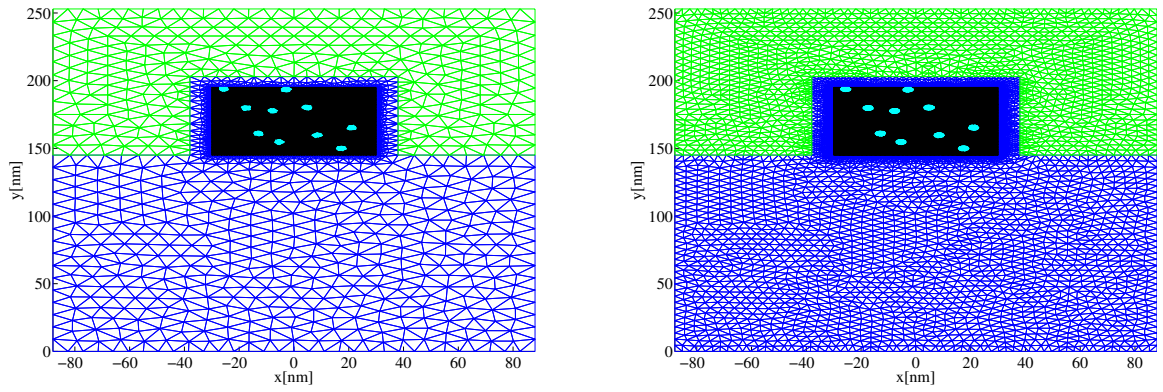

Figure 2: Meshes for the random distribution of impurity atoms (cyan circles) in a nanowire field-effect sensor for levels $\ell = 0$ (left) and $\ell = 1$ (right), where $h_0 = 5$, $r = 2$, and $C_{\mathrm{dop}} = 2 \cdot 10^{17}\,\mathrm{cm}^{-3}$. Additionally, oxide subdomain (D_{ox}), trandsucer (D_{Si}) and the electrolyte (D_{liq}) are depicted with blue, balck and green meshes respectively.

6.2. The Computational Work

As the first step, we calculate the coefficients in the expressions (26) for the computational work. To that end, we solve the system for various mesh sizes and measure the time spent on matrix assembly and solving the resulting

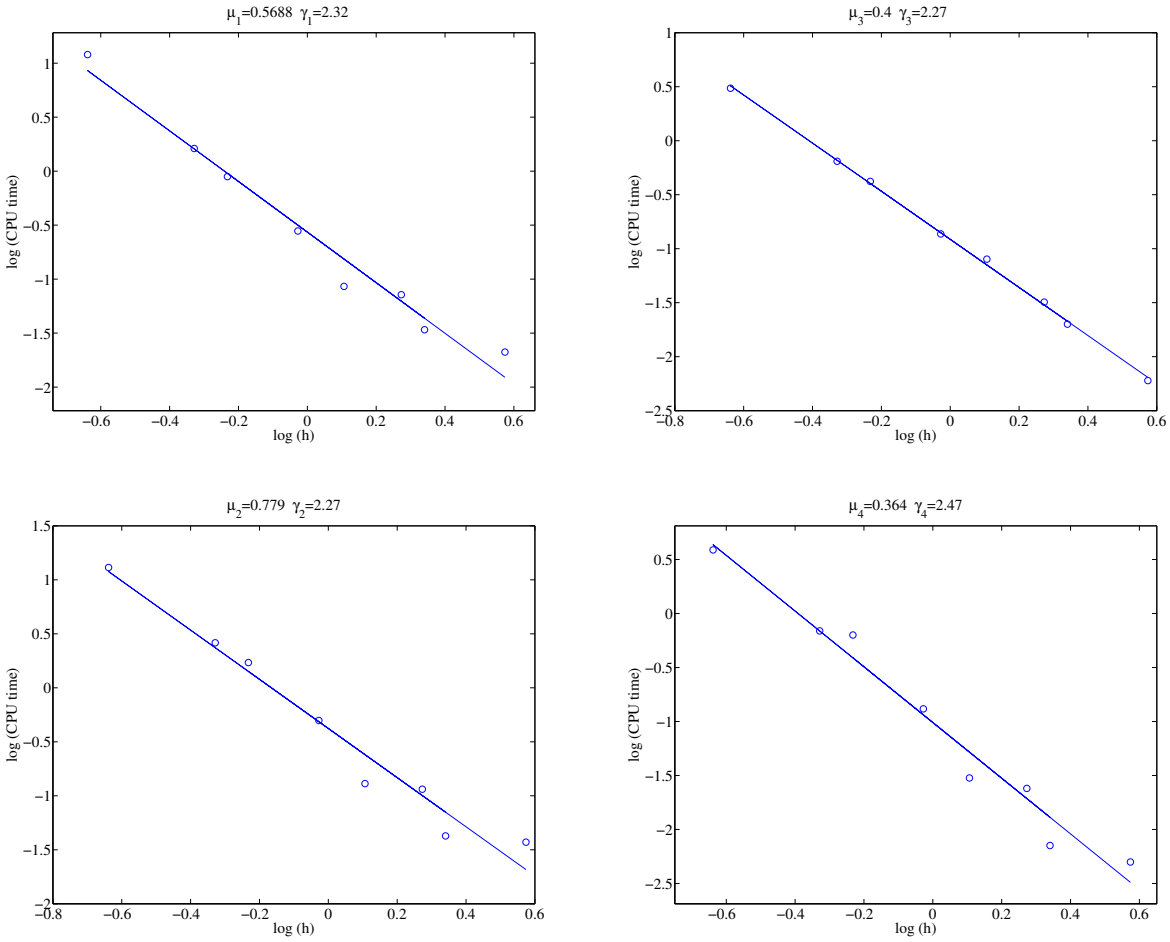

Figure 3: Computational work for matrix assembly (top) and solving the system (bottom), both for the Poisson equation (left) and the drift-diffusion-equations (right).

system, both for the Poisson equation and the drift-diffusion equations. Figure 3 shows the results for the coefficients in the expressions for the computational work.

The coefficients α and C_1 in the FE discretization error

$$\|\mathbb{E}[V - \hat{V}_h]\|_X + \|\mathbb{E}[u - \hat{u}_h]\|_X + \|\mathbb{E}[v - \hat{v}_h]\|_X \leq C_1 h^\alpha$$

of the system are given in Figure 4. The exponent $\alpha = 0.96$ found here agrees very well with the order of the discretization used here, i.e., P_1 finite elements.

For the statistical error, we determine the coefficients in the inequality

$$(\sigma[\Delta V_{h_0}] + \sigma[\Delta V_{h_\ell}]) + (\sigma[\Delta u_{h_0}] + \sigma[\Delta u_{h_\ell}]) + (\sigma[\Delta v_{h_0}] + \sigma[\Delta v_{h_\ell}]) \leq C_{00} + C_0 h_{\ell-1}^\beta.$$

Here $C_{00} = 0.197$ and the rest of the coefficients are shown in Figure 4.

6.3. Optimization

Having determined the coefficients in the expressions for the computational work, it is now possible to numerically solve the optimization problems. As described in Section 5, we apply an iterative interior-point method to optimize both the number of samples and mesh sizes. The results here are obtained for $\xi = 2^{-52}$.

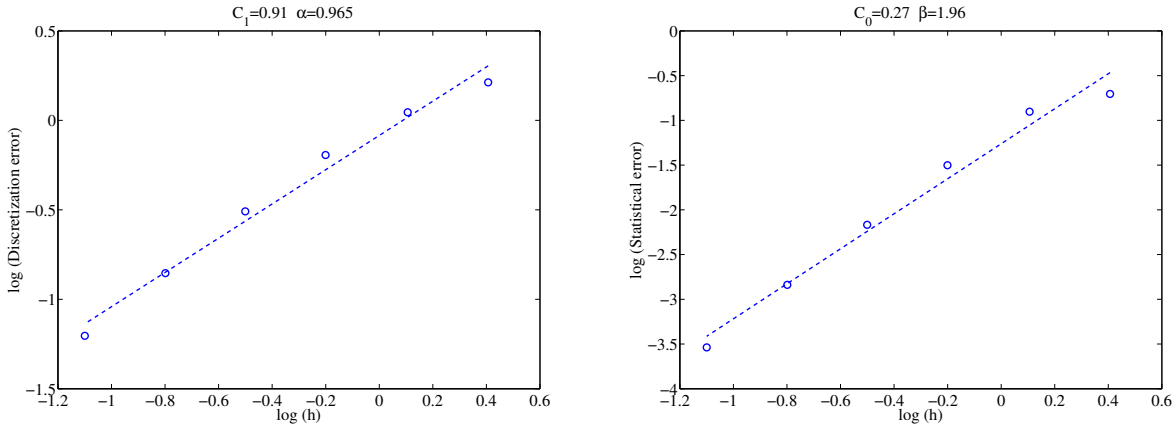

Figure 4: Discretization error (left) and statistical (right) error as a function of h.

6.3.1. Monte Carlo

First of all, we solve the optimization problem (27) for the MC-FE method. Because there is only one level, it is straightforward to solve. The optimal values for the MC FE method are summarized in Table 1 for given ε.

ε	0.1	0.05	0.03	0.02	0.01	0.005	0.002
h	0.054	0.026	0.015	0.010	0.005	0.002	0.001
M	19	77	214	483	1940	7785	48 845

Table 1: Optimal MC FE method parameters for various given error tolerances.

6.3.2. Multi-Level Monte Carlo

In the MLMC-FE method, determining the optimal number of levels is an important part of the calculation. This is achieved here by solving the optimization problem for several levels starting with a single level and noting that the computational work increases above a certain number of levels. More precisely, we solve the optimization problem (31) for $0 \leq L \leq 8$ levels as well as for various given error bounds.

Since the number of samples in each level is a continuous variable in the optimization problem, the optimal number of levels is – in general – not an integer and hence we choose $\lfloor M_\ell \rfloor$, $\ell = 0, \ldots, L$, as the final numbers of levels. Therefore, due to the second constraint g_2, M_ℓ is an integer greater equal 1 for all levels.

The results of the optimization problems provide insight into the MLMC procedure. Figure 5 shows the minimized computational work as a function of the number of levels and as a function of the given tolerance. It shows that for smaller tolerances, more levels are necessary to obtain the smallest computational work.

In Figure 6, the two approaches to multi-level Monte Carlo are compared, namely choosing the h_ℓ as a geometric progressions or freely. Due to generality of the second option, the total work when choosing the h_ℓ freely is lower compared to the first option. The results for both approaches to MLMC-FEM are summarized in Tables 2 and 3 for various given error tolerances.

6.3.3. Comparison

Finally, as Figure 7 shows, the computational work for the multi-level Monte-Carlo method is approximately 10 times lower than the one for the Monte-Carlo method for larger tolerance levels such as $\varepsilon = 0.1$. The effectiveness of the MLMC-FE method is more pronounced for smaller error bounds; for $\varepsilon = 0.005$, the computational work is about a factor 10^4 lower than the Monte-Carlo work.

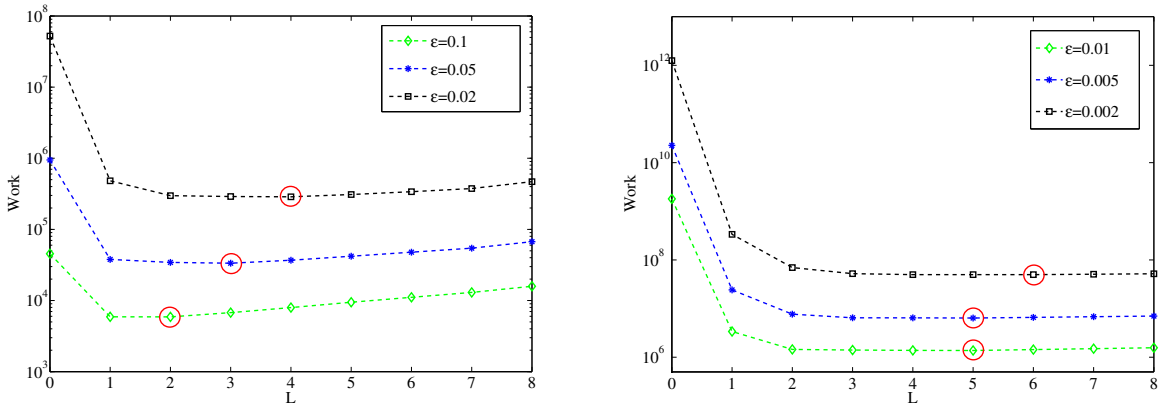

Figure 5: The minimized computational work for the MLMC-FE method as a function of the number of levels and as a function of the given error tolerance. The results for a geometric progression for h (left) and general h (right) are shown. The number of levels yielding the minimal overall computational work is indicated by red circles.

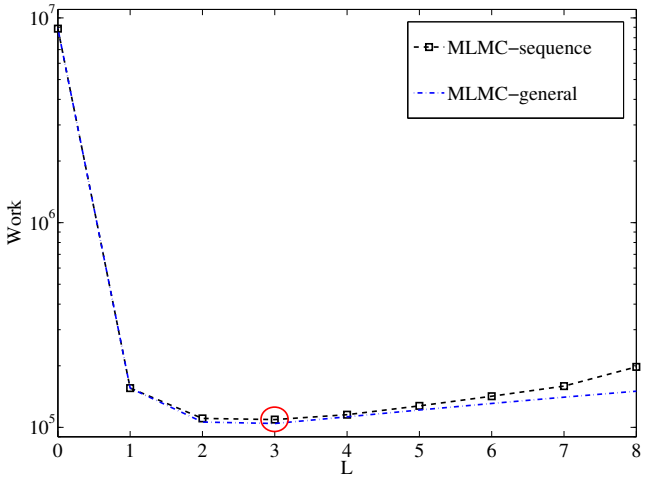

Figure 6: Comparison between the two different approaches to MLMC FE method for $\varepsilon = 0.03$.

The optimal distribution of the samples among the levels in the multi-level method leads to more evaluations in the first levels (which are cheaper) and to fewer evaluations in the higher levels. On the other hand, to satisfy the first constraint of (27), the Monte-Carlo method needs a smaller mesh size compared to the multi-level method, which greatly increases the total computational work although the total number of samples is lower.

7. Conclusions

In this work, we considered the stochastic drift-diffusion-Poisson equations as the main model equation for describing transport in random environments with many applications. We presented existence and local uniqueness theorems for the weak solution of the system. We also developed MC- and MLMC-FE methods for this system of stochastic PDEs.

Additionally, we balanced the various parameters in the numerical methods by viewing this problem as a global

ε	h_0	r	M_0	M_1	M_2	M_3	M_4	M_5	M_6
0.1	0.359	2.650	59	4	1	–	–	–	–
0.05	0.350	2.430	276	22	2	1	–	–	–
0.03	0.329	2.830	779	46	2	1	–	–	–
0.02	0.339	2.440	1 993	152	12	1	1	–	–
0.01	0.347	2.355	9 428	786	69	6	1	1	–
0.005	0.332	2.670	39 142	2 526	154	9	1	1	–
0.002	0.334	2.647	286 181	18 986	1200	76	6	1	1

Table 2: Optimal levels for the MLMC-FE method with h_ℓ chosen as a geometric progression for given error tolerances ε.

ε	h_0	r_1	r_2	r_3	r_4	r_5	r_6
0.1	0.366	2.100	3.490	–	–	–	–
0.05	0.360	2.168	1.860	3.712	–	–	–
0.03	0.343	2.351	2.138	4.750	–	–	–
0.02	0.346	2.317	2.086	1.744	4.348	–	–
0.01	0.339	2.400	2.218	1.938	1.536	4.554	–
0.005	0.332	2.483	2.348	2.134	1.812	6.220	–
0.002	0.328	2.541	2.442	2.280	2.030	1.670	7.142

ε	M_0	M_1	M_2	M_3	M_4	M_5	M_6
0.1	59	6	1	–	–	–	–
0.05	280	28	4	1	–	–	–
0.03	800	66	7	1	–	–	–
0.02	2 012	171	19	3	1	–	–
0.01	8 897	697	66	8	2	1	–
0.005	38 251	2 778	229	24	4	1	–
0.002	271 031	18 667	1408	124	14	3	1

Table 3: Optimal levels for the MLMC-FE method with general h_ℓ for given error tolerances ε.

optimization problem. The goal is to determine the numerical parameters such that the computational work to achieve a total error, i.e., discretization error plus statistical error, less than or equal to a given error tolerance is minimized.

Although the exponential terms in the constraints make the optimization problems nonlinear, the optimization problems can be solved by an interior-point method with sufficient iterations. The solution of the constrained optimization problem leads to optimal $(M,\ h)$ in the case of the vanilla MC method and to hierarchies consisting of $(L, \{M_\ell\}_{\ell=0}^{L}, h_0, r)$ in the case of the MLMC method.

Moreover, we investigated two different options to the mesh refinement in the multi-level method. In the comparison of the MC with the MLMC method, the MLMC method was found to decrease the total computational effort by four orders of magnitude for small error tolerances. The speed-up becomes better as the error tolerance decreases.

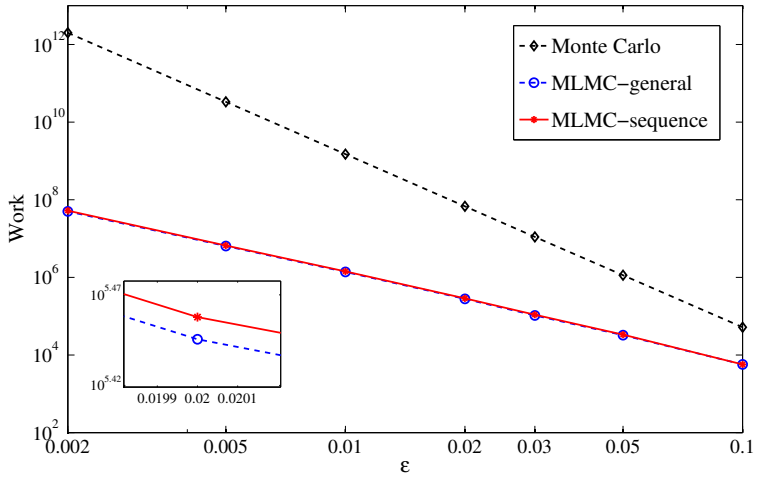

Figure 7: Comparison of total computational work for MC-FEM and the two approaches to MLMC-FEM for various given tolerances.

8. Acknowledgments

The authors acknowledge support by FWF (Austrian Science Fund) START project no. Y660 *PDE Models for Nanotechnology*. The authors acknowledge discussions with Dr. Masoud Ahookhosh (University of Luxembourg) about numerical optimization methods.

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